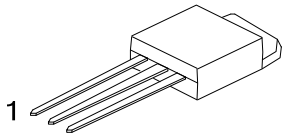
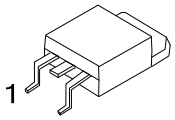
4N65-TC1

Power MOSFET

4A, 650V N-CHANNEL POWER MOSFET



TO-251



TO-252

■ DESCRIPTION

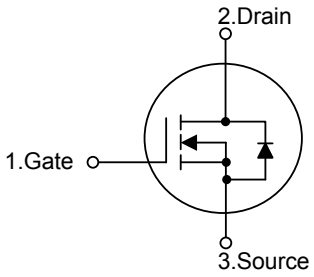
The UTC **4N65-TC1** is a N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology allows a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **4N65-TC1** is generally applied in high efficiency switch mode power supplies.

■ FEATURES

* $R_{DS(ON)} \leq 2.7\Omega$ @ V_{GS}=10V, I_D=2.0A
* High Switching Speed

■ SYMBOL



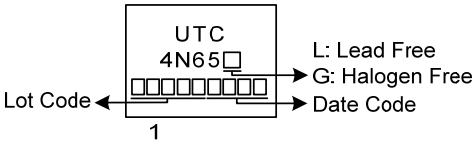
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
4N65L-TM3-T	4N65G-TM3-T	TO-251	G	D	S	Tube
4N65L-TN3-R	4N65G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

4N65G-TM3-T (1)Packing Type (2)Package Type (3)Green Package	(1) T: Tube, R: Tape Reel (2) TM3: TO-251, TN3: TO-252 (3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	4	A
	Pulsed (Note 2)	I_{DM}	8	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	105	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.45	V/ns
Power Dissipation		P_D	50	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 10mH, I_{AS} = 4.6A, V_{DD} = 50V, R_G = 25 Ω Starting T_J = 25°C
4. I_{SD} ≤ 4.0A, di/dt ≤100A/μs, V_{DD} ≤BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	110	°C/W
Junction to Case	θ_{JC}	2.5 (Note)	°C/W

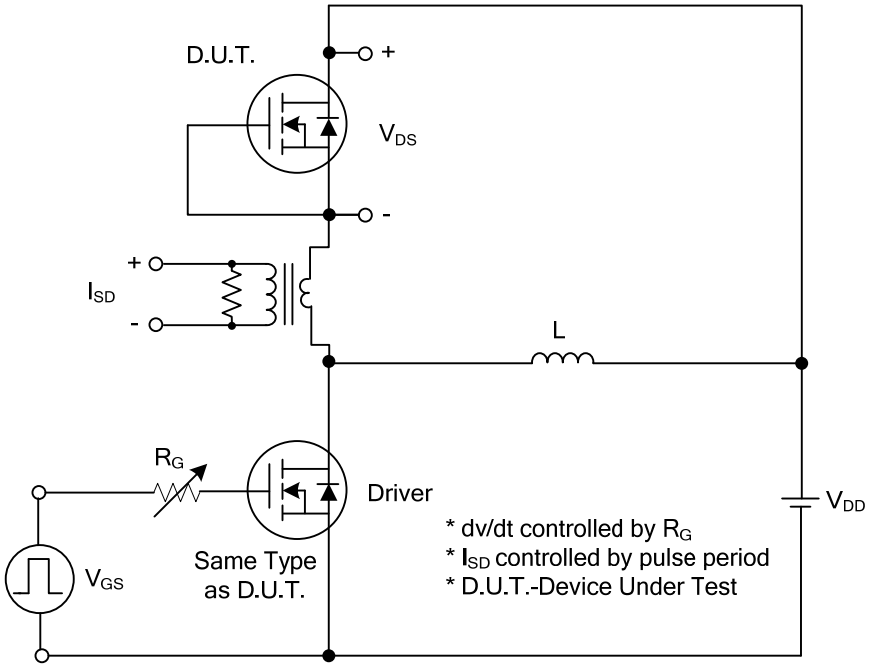
Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

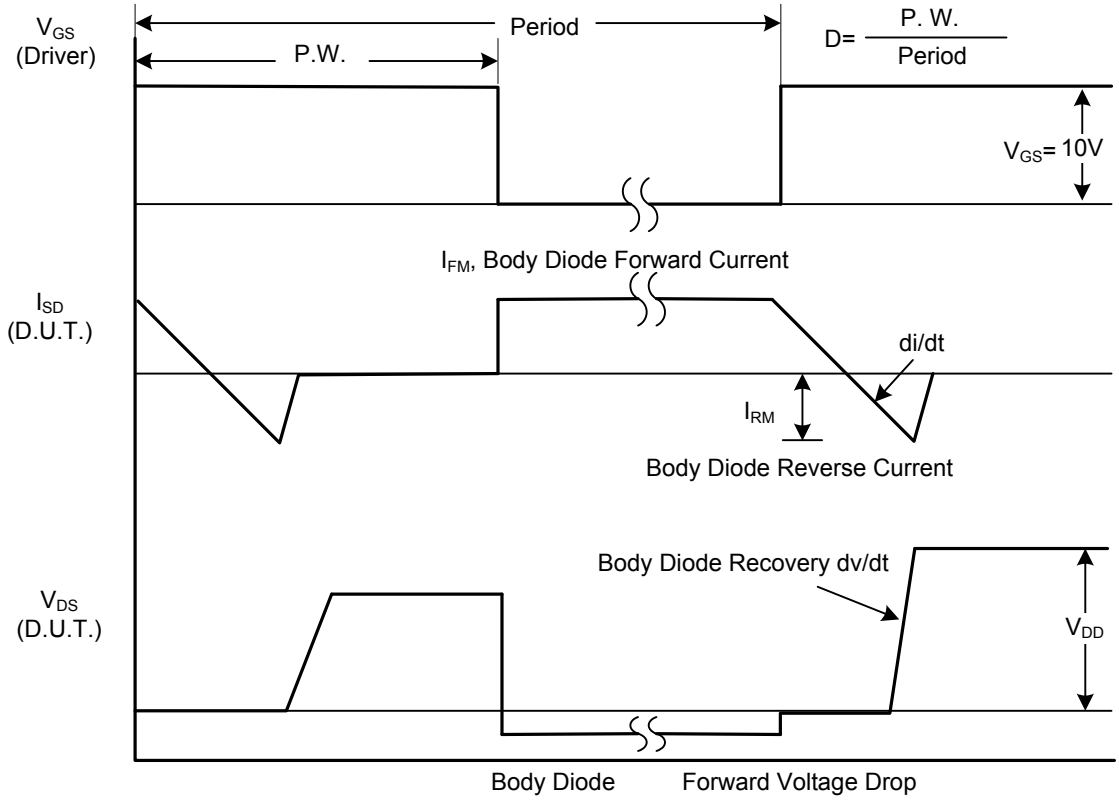
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D= 250μA	650			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=650V, V_{GS}=0V			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=30V, V_{DS}=0V			100	nA
	Reverse		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=2.0A			2.7	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0 MHz		532		pF
Output Capacitance		C_{OSS}			57		pF
Reverse Transfer Capacitance		C_{RSS}			3.5		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge (Note 1)		Q_G	V_{DS}=520V, V_{GS}=10V, I_D=4A I_G=1mA (Note 1, 2)		15		nC
Gateource Charge		Q_{GS}			4.9		nC
Gate-Drain Charge		Q_{GD}			3		nC
Turn-on Delay Time (Note 1)		$t_{D(ON)}$	V_{DS}=100V, V_{GS}=10V, I_D=4A, R_G=25Ω (Note 1, 2)		5.6		ns
Rise Time		t_R			16.5		ns
Turn-off Delay Time		$t_{D(OFF)}$			37		ns
Fall-Time		t_F			26.5		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Continuous Drain-Source Diode Forward Current		I_S				4	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				8	A
Drain-Source Diode Forward Voltage (Note 1)		V_{SD}	I_S=4A, V_{GS}=0V			1.4	V
Reverse Recovery Time (Note 1)		t_{rr}	I_S=4A, V_{GS}=0V dI_F/dt=100A/μs (Note1)		332		ns
Reverse Recovery Charge		Q_{rr}			1.7		μC

Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

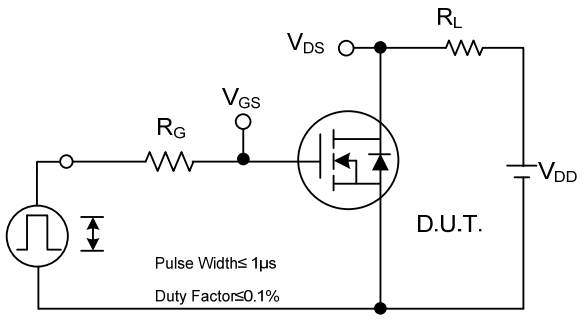


Peak Diode Recovery dv/dt Test Circuit

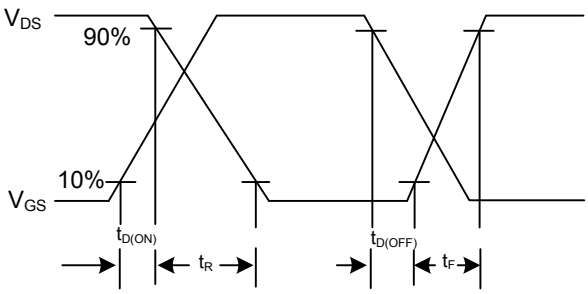


Peak Diode Recovery dv/dt Waveforms

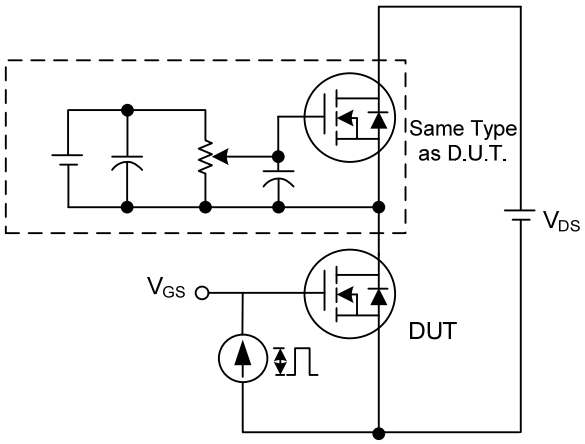
■ TEST CIRCUITS AND WAVEFORMS



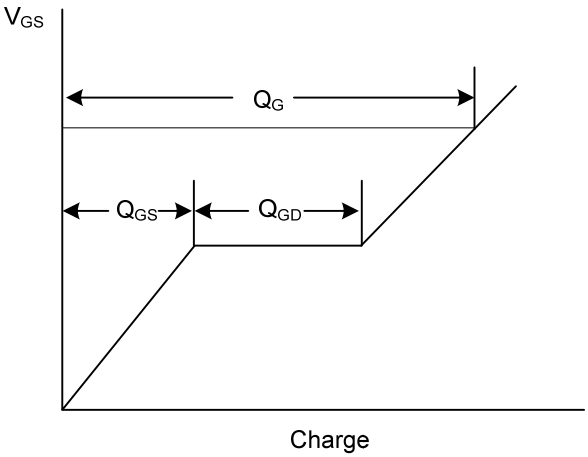
Switching Test Circuit



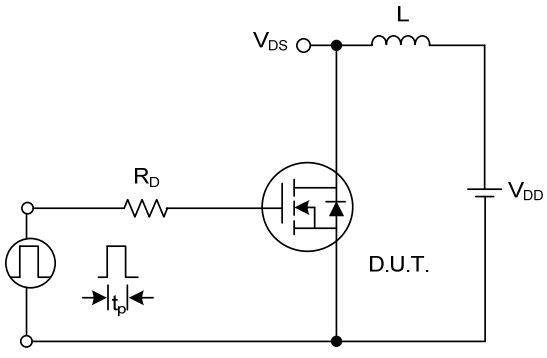
Switching Waveforms



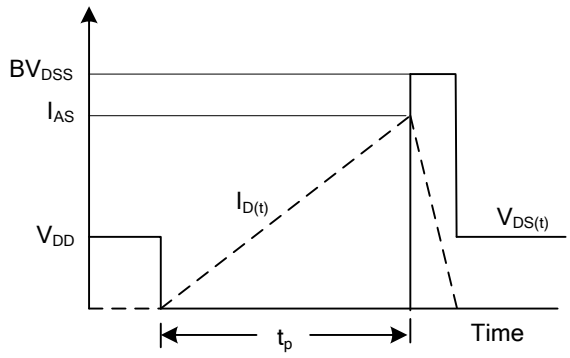
Gate Charge Test Circuit



Gate Charge Waveform



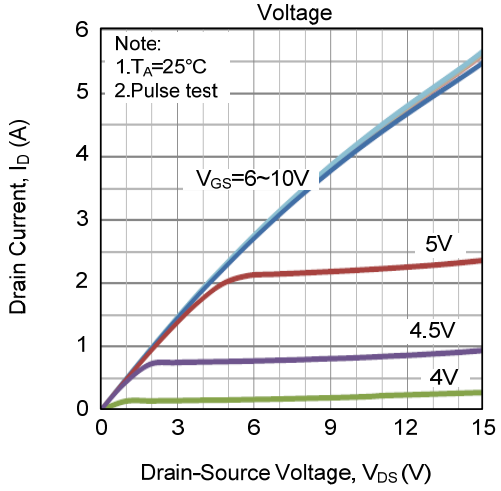
Unclamped Inductive Switching Test Circuit



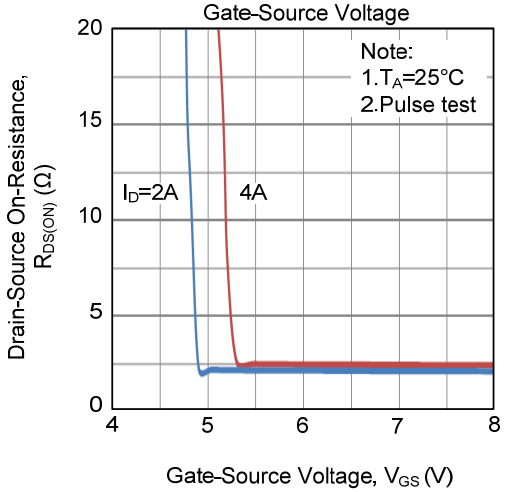
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

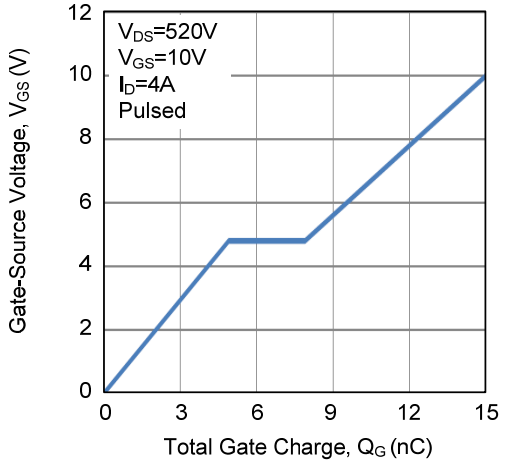
Drain Current vs. Drain-Source Voltage



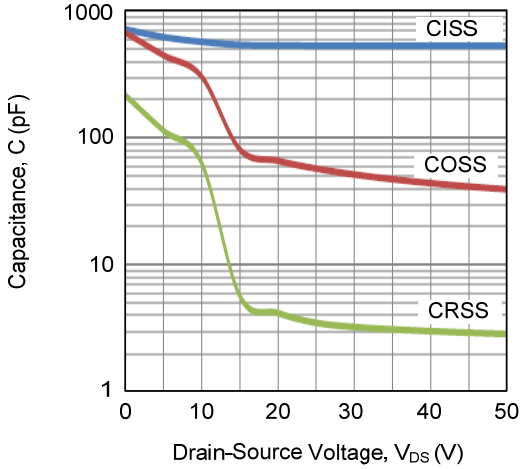
Drain-Source On-Resistance vs. Gate-Source Voltage



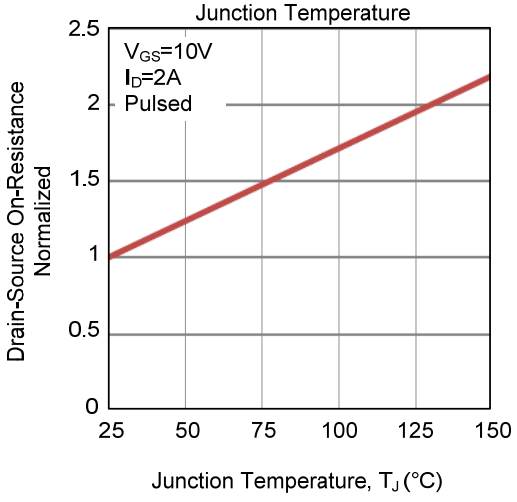
Gate Charge Characteristics



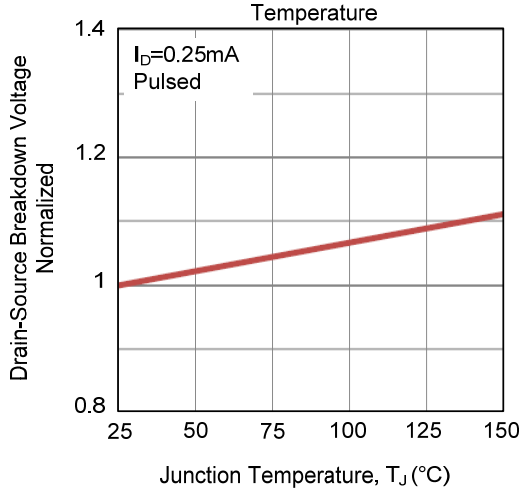
Capacitance Characteristics



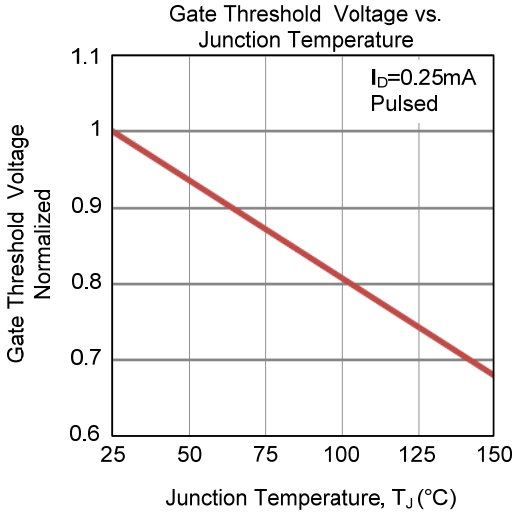
Drain-Source On-Resistance vs. Junction Temperature

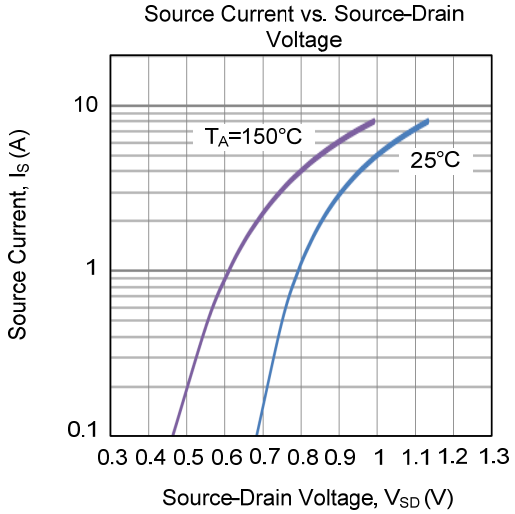


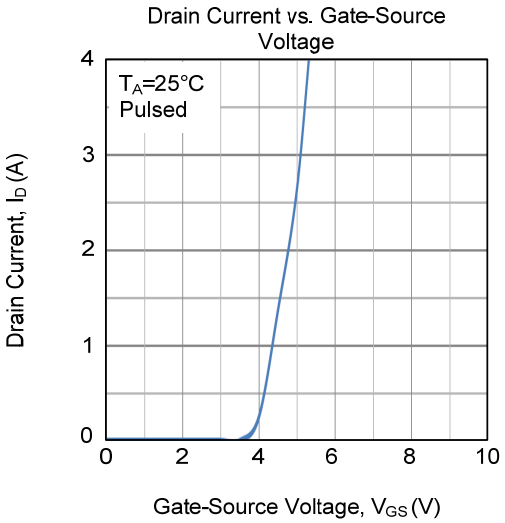
Breakdown Voltage vs. Junction Temperature

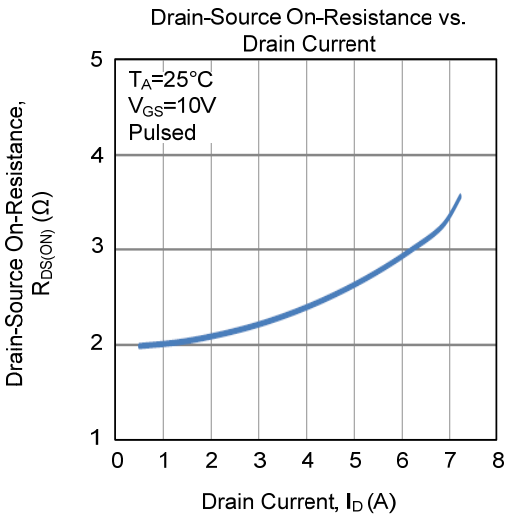


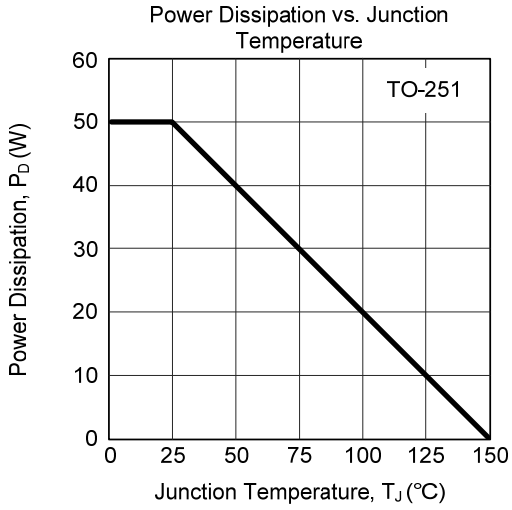
■ TYPICAL CHARACTERISTICS (Cont.)

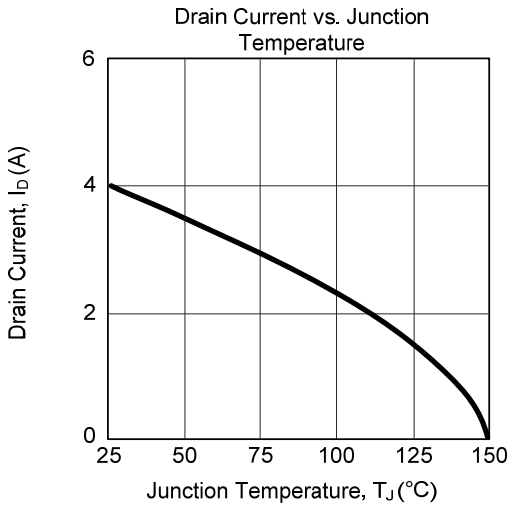












■ TYPICAL CHARACTERISTICS (Cont.)